

2SB939, 2SB939A

Silicon PNP epitaxial planar type Darlington

For midium-speed power switching

Complementary to 2SD1262 and 2SD1262A

Features

- High foward current transfer ratio h_{FE}
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-60	V
2SB939 2SB939A		-80	
Collector to emitter voltage	V _{CEO}	-60	V
2SB939 2SB939A		-80	
Emitter to base voltage	V _{EBO}	-7	V
Peak collector current	I _{CP}	-12	A
Collector current	I _C	-8	A
Collector power dissipation	P _C	T _C =25°C	45
		T _a =25°C	1.3
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -60V, I _E = 0			-100	μA
		V _{CB} = -80V, I _E = 0			-100	
Emitter cutoff current	I _{EBO}	V _{EB} = -7V, I _C = 0			-2	mA
Collector to emitter voltage	V _{CEO}	I _C = -30mA, I _B = 0	-60			V
			-80			
Forward current transfer ratio	h _{FE1} *	V _{CE} = -3V, I _C = -4A	2000		10000	
	h _{FE2}	V _{CE} = -3V, I _C = -8A	500			
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -4A, I _B = -8mA			-1.5	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = -4A, I _B = -8mA			-2	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -0.5A, f = 1MHz		15		MHz
Turn-on time	t _{on}	I _C = -4A, I _{B1} = -8mA, I _{B2} = 8mA, V _{CC} = -50V		0.5		μs
Storage time	t _{stg}			2		μs
Fall time	t _f			1		μs

*h_{FE1} Rank classification

Rank	Q	P
h _{FE1}	2000 to 5000	4000 to 10000

Internal Connection





